

PNP TRANSISTORS



TO-92/TO-226AA

'2N' and 'TP' DEVICE TYPES

ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

Device Type	I_C Max. (mA)	$V_{(BR)CBO}$ (V)	$V_{(BR)CEO}$ (V)	$V_{(BR)EBO}$ (V)	I_{CBO}		DC Current Gain				$V_{CE(sat)}$		f_T		C_{ob}^1 (pF)	t_s^1 (ns)	NF ¹ (dB)	Pinning 1, 2, 3
					Max. (nA)	@ V_{CB} (V)	h_{FE} Min.	h_{FE} Max.	@ I_C (mA)	@ V_{CE} (V)	Max. (V)	@ I_C (mA)	Min. (MHz)	@ I_C (mA)				
TP2907A	500	60	60	5.0	10	50	100	300	150	10	0.4	150	200	50	8.0	100	—	EBC
2N3906	200	40	40	5.0	—	—	100	300	10	1.0	0.25	10	250	10	4.5	225	4.0	EBC
2N4403	500	40	40	5.0	—	—	100	300	150	2.0	0.4	150	200	20	10	225	—	EBC
2N5401	300	160	150	5.0	50	120	60	240	10	5.0	0.2	10	100	10	6.0	—	8.0	EBC
MPSA56	800	80	80	4.0	100	80	50	—	100	1.0	0.25	100	50	100	—	—	—	EBC

NOTES: 1) Maximum at typical JEDEC conditions.

2) $V_{(BR)CES}$